



Figure S1. Schematic of the fabricated device with the present nanowires: (a) without tunnel junction. (b) with p^{++} -GaN/InGaN/n⁺⁺-GaN TJ. (c) TEM and dark field STEM images show the successful TJ embedded in the structure. (d) photoresponse of the PEC-PD under 302 nm and 405 nm with power density of 1.6 mW cm⁻² and 4.5 mW cm⁻², respectively.